

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

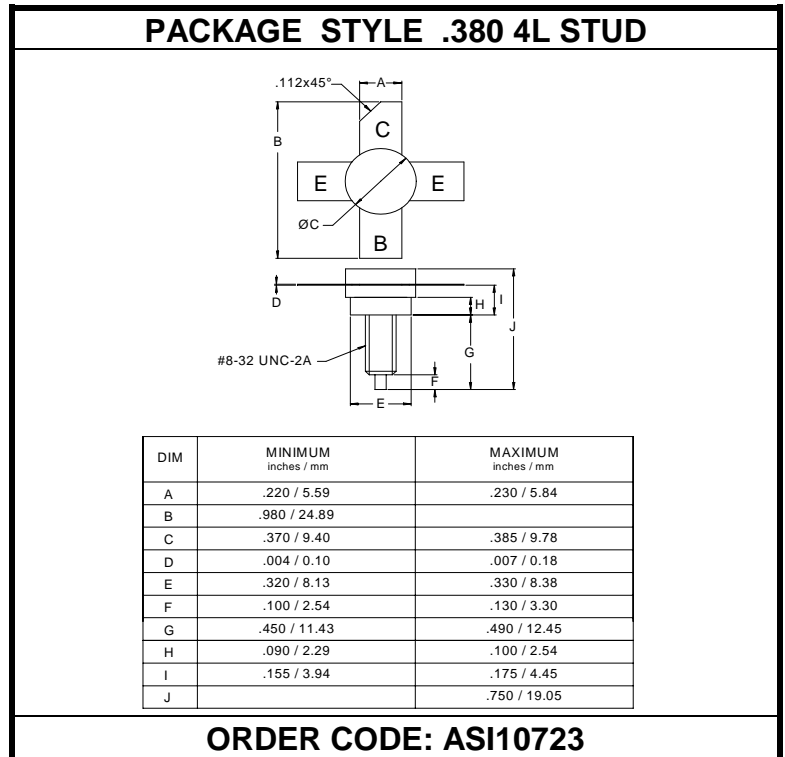
The **ASI VHB10-28S** is Designed for Class C, 28 V High Band Applications up to 175 MHz.

FEATURES:

- Common Emitter
- $P_G = 10$ dB at 10W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

| | |
|---------------|-------------------|
| I_C | 1.0 A |
| V_{CBO} | 65 V |
| V_{CEO} | 35 V |
| V_{CES} | 65 V |
| V_{EBO} | 4.0 V |
| P_{DISS} | 13.0 W |
| T_J | -65 °C to +200 °C |
| T_{STG} | -65 °C to +150 °C |
| θ_{JC} | 5.5 °C/W |


CHARACTERISTICS $T_C = 25^\circ\text{C}$

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|-------------------|--|---------|---------|---------|---------|
| BV_{CBO} | $I_C = 200$ mA | 65 | | | V |
| BV_{CES} | $I_C = 200$ mA | 65 | | | V |
| BV_{CEO} | $I_C = 200$ mA | 35 | | | V |
| BV_{EBO} | $I_E = 10$ mA | 4.0 | | | V |
| I_{CBO} | $V_{CB} = 30$ V | | | 1.0 | mA |
| h_{FE} | $V_{CE} = 5.0$ V $I_C = 200$ mA | 5.0 | | --- | --- |
| C_{ob} | $V_{CB} = 28$ V $f = 1.0$ MHz | | | 15 | pF |
| P_G η_C | $V_{CC} = 28$ V $P_{OUT} = 10$ W $f = 175$ MHz | 10 | 60 | | dB % |